

N-channel TrenchMOS SiliconMAX standard level FET Rev. 4 — 12 January 2012 Product de

Product data sheet

Product profile 1.

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- applications due to fast switching characteristics

Suitable for high frequency

1.3 Applications

Out all set and a set of a factor

Table 4

DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>	-	-	47	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	150	W
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	22	25	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 45 A; V _{DS} = 80 V; T _j = 25 °C; see <u>Figure 13</u>	-	25	-	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain ^[1]	mb	
3	S	source		
mb	D mounting base; connected to drain		mbb076 S	
			SOT428 (DPAK)	

[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN025-100D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

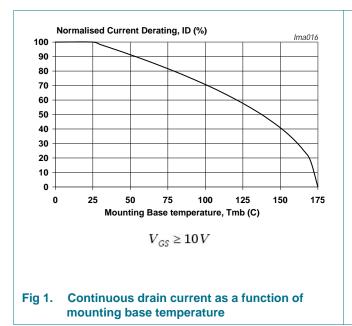
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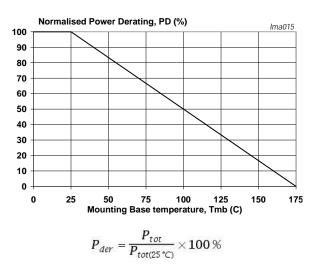
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	T _j ≤ 175 °C; T _j ≥ 25 °C; R _{GS} = 20 kΩ	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	33	А
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } Figure 1;$ see Figure 4	-	47	A
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C; see <u>Figure 4</u>	-	188	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dra	ain diode				
I _S	source current	T _{mb} = 25 °C	-	47	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	188	А
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	260	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; R_{GS} = 50 \Omega; unclamped; see Figure 3$	-	47	A



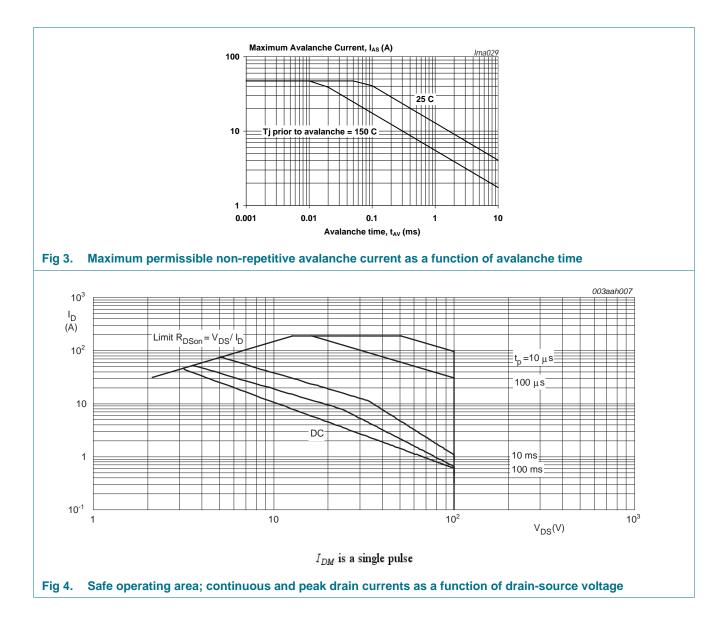




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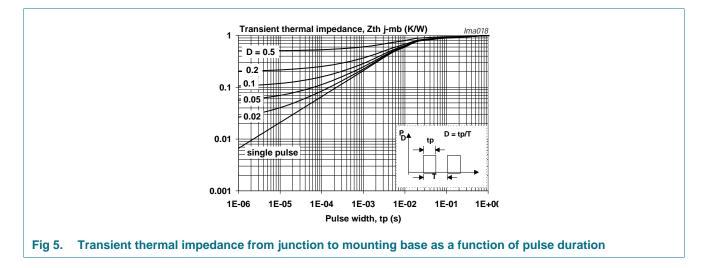
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Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 5	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	SOT428 package ; printed-circuit board mounted ; minimum footprint	-	50	-	K/W



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6. Characteristics

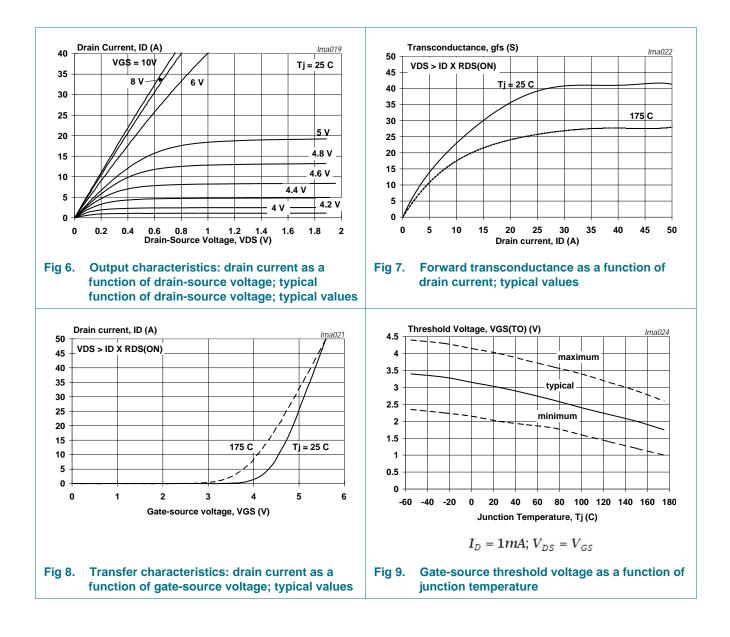
Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 9</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 9</u>	-	-	6	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	- 0.05 10	μΑ	
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μΑ
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	0.02	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 11</u>	-	-	68	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	22	25	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q_{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{1000}$	-	13	-	nC
Q_{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	2600	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{1000}$	-	340	-	pF
C _{rss}	reverse transfer capacitance		-	195	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 1.8 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_{j} = 25 \ ^{\circ}C$	-	72	-	ns
t _{d(off)}	turn-off delay time		-	69	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; $T_j = 25 \ ^{\circ}C$	-	3.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.87	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/µs;	-	82	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C$	-	0.26	-	μC

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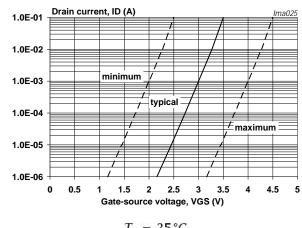
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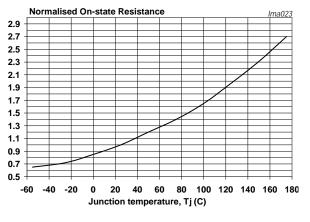
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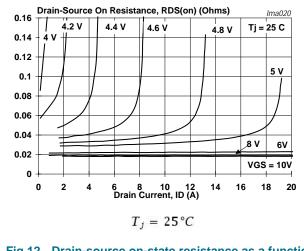
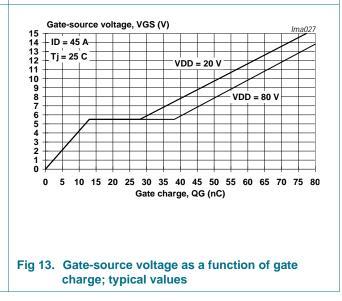




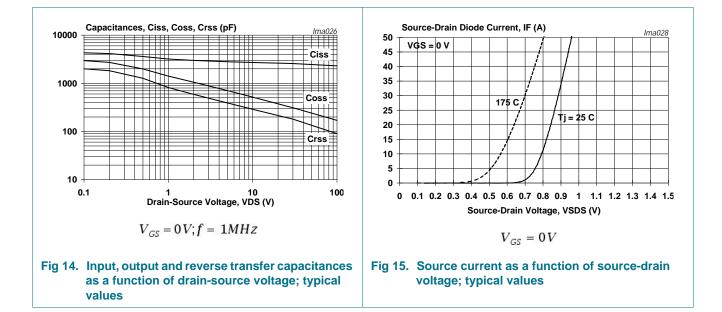
Fig 11. Normalized drain source on-state resistance factor as a function of junction temperature



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7. Package outline

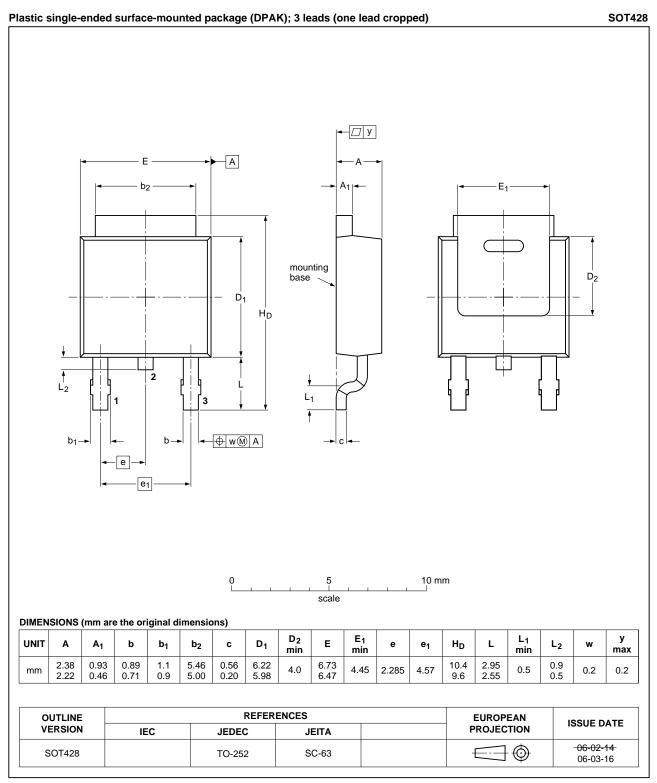


Fig 16. Package outline SOT428 (DPAK)

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN025-100D v.4	20120112	Product data sheet	-	PSMN025-100D v.3
Modifications:	 Various changes 	to content.		
PSMN025-100D v.3	20081120	Product data sheet	-	PSMN025-100D v.2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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